

2SK1620(L), 2SK1620(S)

Silicon N-Channel MOS FET

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Application

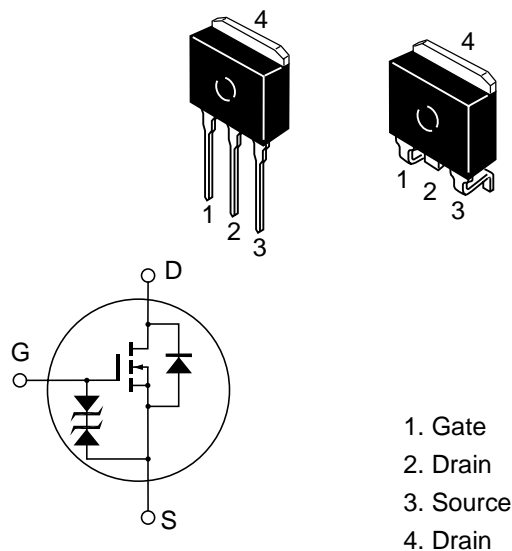
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC converter and motor driver

Outline

LDBPAK



2SK1620(L), 2SK1620(S)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	150	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	10	A
Drain peak current	$I_{D(pulse)}^{*1}$	40	A
Body to drain diode reverse drain current	I_{DR}	10	A
Channel dissipation	P_{ch}^{*2}	50	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

- Notes 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$

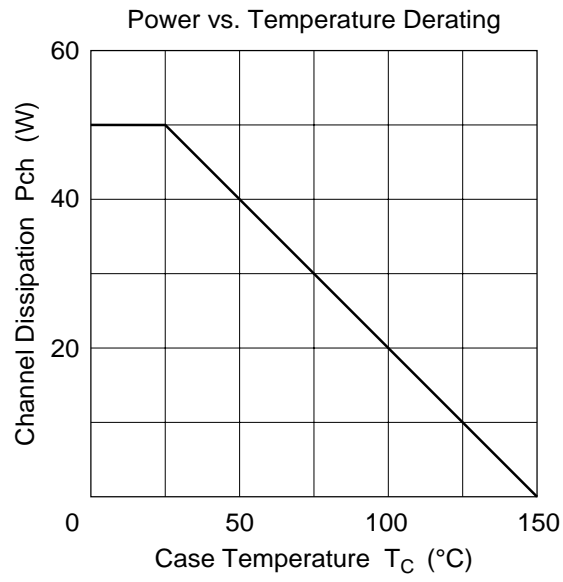
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	150	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	250	μA	$V_{DS} = 120 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	4.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static Drain to source on state resistance	$R_{DS(on)}$	—	0.12	0.15	Ω	$I_D = 5 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	4.0	7.0	—	S	$I_D = 5 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	1200	—	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	C_{oss}	—	550	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	C_{rss}	—	85	—	pF	
Turn-on delay time	$t_{d(on)}$	—	20	—	ns	$I_D = 5 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	t_r	—	50	—	ns	$R_L = 6 \text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	—	70	—	ns	
Fall time	t_f	—	40	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.2	—	V	$I_F = 10 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	220	—	ns	$I_F = 10 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu\text{s}$

Note 1. Pulse test

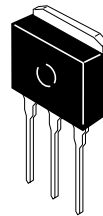
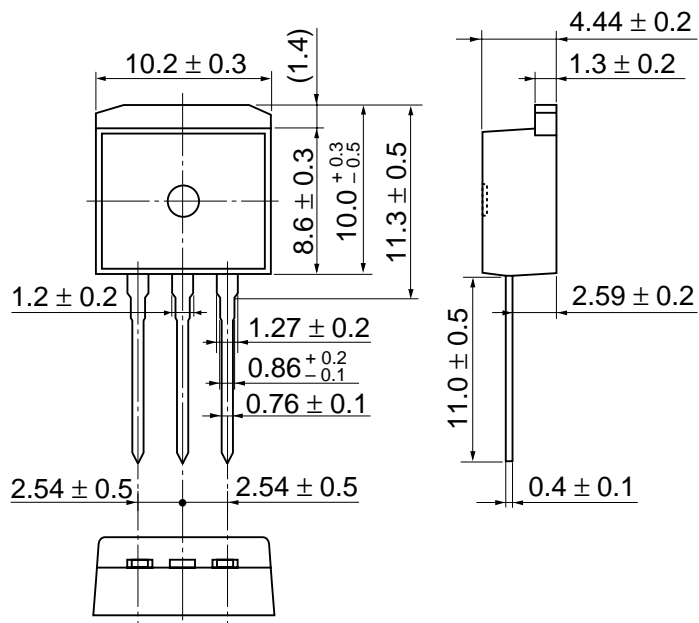
See characteristic curves of 2SK740.

2SK1620(L), 2SK1620(S)



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Unit: mm



Hitachi Code	LPAK (L)
JEDEC	—
EIAJ	—
Weight (reference value)	1.4 g

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